

Ordering number : ENA0661



SANYO Semiconductors

DATA SHEET

P-Channel Silicon MOSFET

# EMH1303 — General-Purpose Switching Device Applications

## Features

- Low ON-resistance.
- 1.8V drive.

## Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		-12	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±10	V
Drain Current (DC)	I <sub>D</sub>		-7	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	-28	A
Allowable Power Dissipation	P <sub>D</sub>	Mounted on a ceramic board (1200mm²×0.8mm)	1.5	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =-1mA, V <sub>GS</sub> =0V	-12			V
Zero-Gate Voltage Drain Current	I <sub>DSS1</sub>	V <sub>DS</sub> =-8V, V <sub>GS</sub> =0V			-1	μA
	I <sub>DSS2</sub>	V <sub>DS</sub> =-12V, V <sub>GS</sub> =0V			-10	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =-6V, I <sub>D</sub> =-1mA	-0.4		-1.2	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =-6V, I <sub>D</sub> =-3A	7.2	12		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =-6A, V <sub>GS</sub> =-4.5V		18	23	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =-6A, V <sub>GS</sub> =-2.5V		27	36	mΩ
	R <sub>DS(on)3</sub>	I <sub>D</sub> =-0.5A, V <sub>GS</sub> =-1.8V		40	65	mΩ

Marking : JC

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# EMH1303

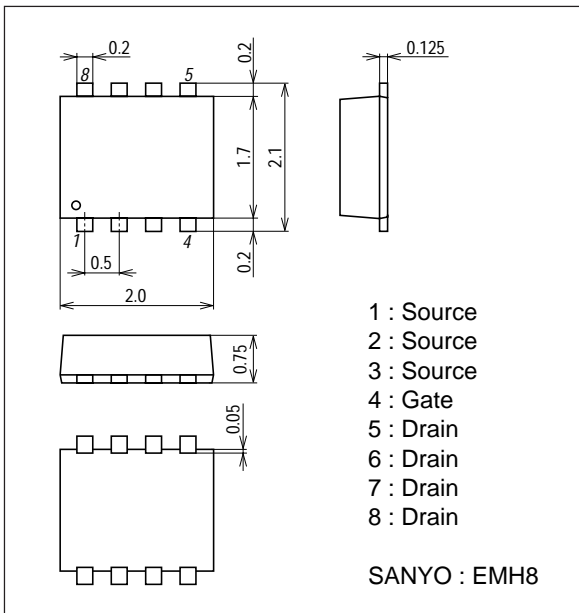
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	$V_{DS}=-6V, f=1MHz$		1100		pF
Output Capacitance	Coss	$V_{DS}=-6V, f=1MHz$		350		pF
Reverse Transfer Capacitance	Crss	$V_{DS}=-6V, f=1MHz$		265		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit.		11		ns
Rise Time	$t_r$	See specified Test Circuit.		165		ns
Turn-OFF Delay Time	$t_d(off)$	See specified Test Circuit.		100		ns
Fall Time	$t_f$	See specified Test Circuit.		105		ns
Total Gate Charge	Qg	$V_{DS}=-6V, V_{GS}=-4.5V, I_D=-7A$		12.0		nC
Gate-to-Source Charge	Qgs	$V_{DS}=-6V, V_{GS}=-4.5V, I_D=-7A$		1.9		nC
Gate-to-Drain "Miller" Charge	Qgd	$V_{DS}=-6V, V_{GS}=-4.5V, I_D=-7A$		2.9		nC
Diode Forward Voltage	VSD	$I_S=-7A, V_{GS}=0V$		-0.8	-1.2	V

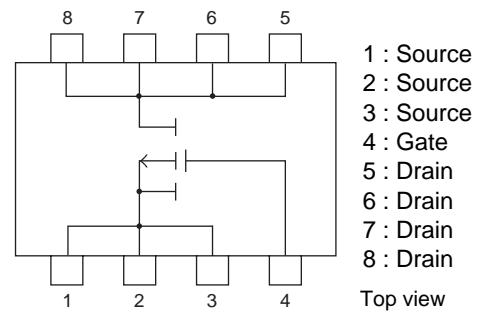
## Package Dimensions

unit : mm (typ)

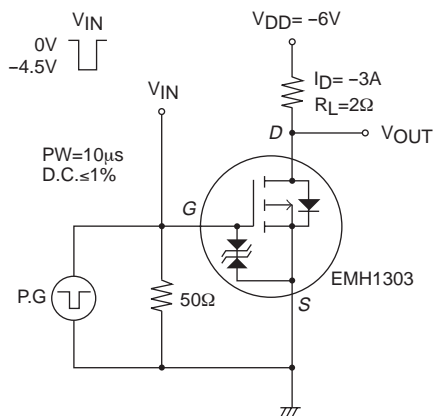
7045-001



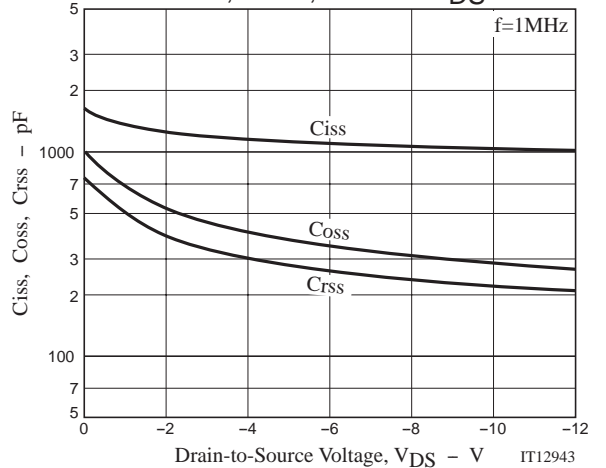
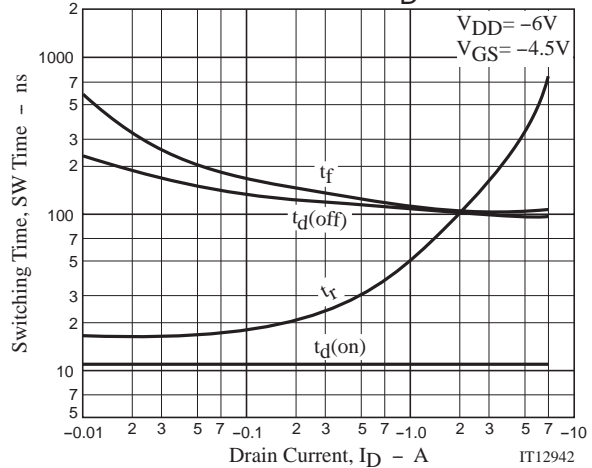
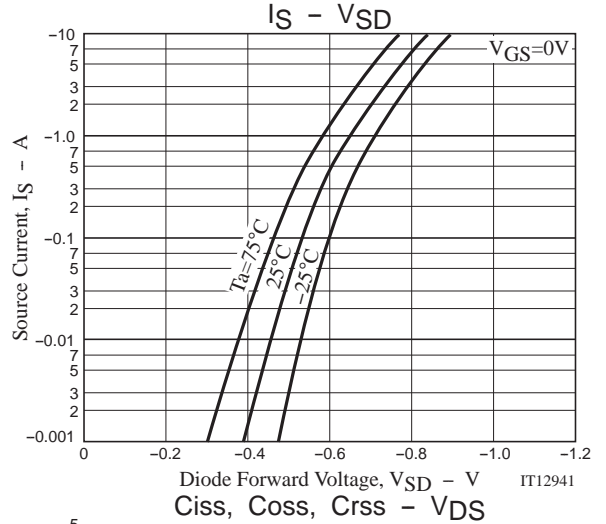
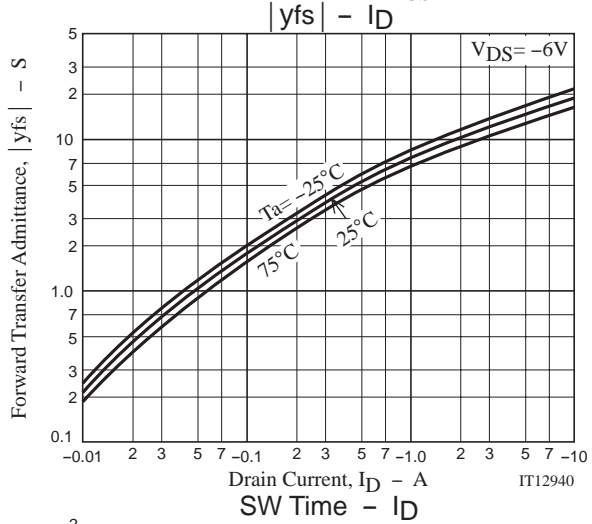
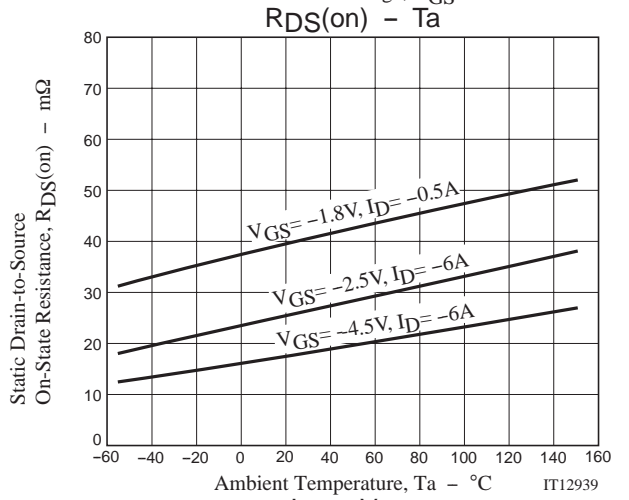
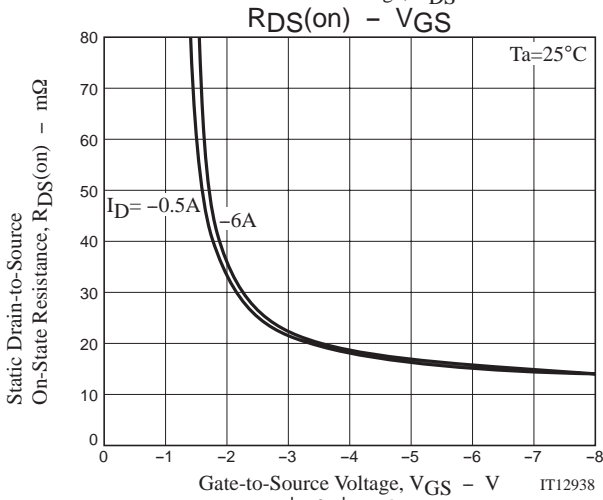
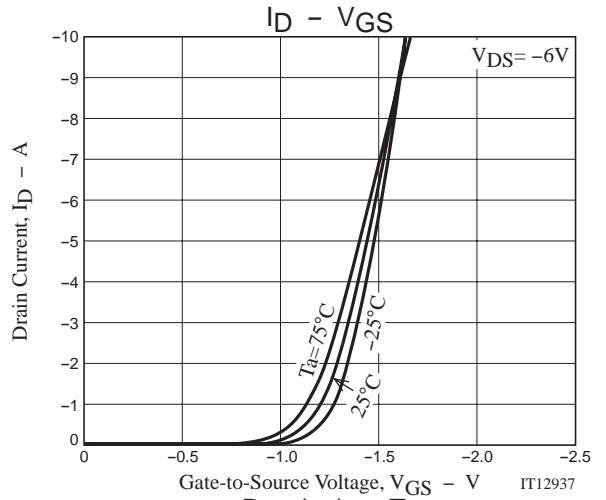
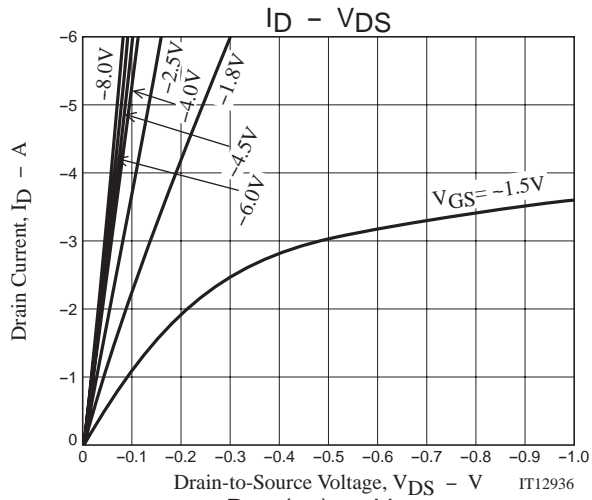
## Electrical Connection



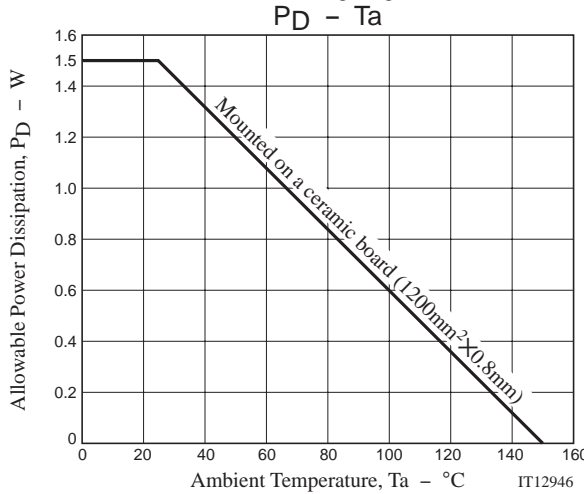
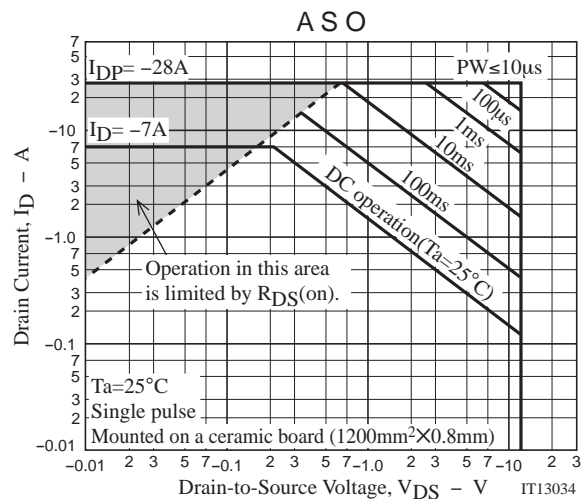
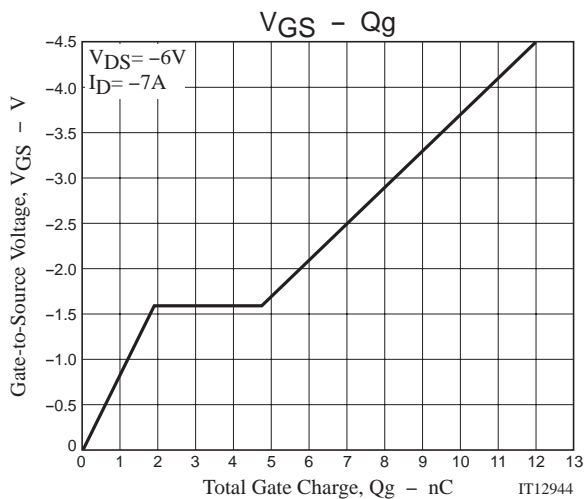
## Switching Time Test Circuit



# EMH1303



# EMH1303



Note on usage : Since the EMH1303 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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